

INSPECTION METHOD TO CHECK CONTACT HOLE OPEN AFTER CONTACT ETCHING

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Abstract of the Invention

10 The present invention provides an inspection method including the following steps. First, the wafer, after contact etching, will carry out a SEM's (scanning electron microscope) scanning electron beam, wherein the amplification factor is about 500 to 5000 and the scanning time is about 5 to 10 second. The surface of silicon, silicon oxide, or other insulating materials may display different color after processing electron beam scanning due to the different material charging effect. Therefore, the etching result may be determined by comparing the color shown on the SEM photograph.

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